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SECTION I—SPECIFICATION AMENDMENTS

Please amend the specification as shown below:

Please replace the paragraph beginning at page 5, line 15, with the following amended paragraph:

Figure 1B illustrates the state of the wafer after the conductive layer 114 is removed. Starting with the wafer as shown in Figure 1A, the conductive layer 114 is removed from the field using electro-polish, chemical polishing or CMP. At the conclusion of the removal of the conductive layer, conductive material remains inside the feature 104, separated from the ILD layer 102 by the under-layer 110 and the barrier layer 112. The portion of the conductive layer that previously covered the field surrounding the feature is substantially removed, leaving only the under-layer 110 and the barrier layer 112 in the field. ~~This patent addresses the process of removing the barrier layer 112 that is the exposed in Figure 1B after the bulk of the conductive layer 114 has been removed.~~

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